



## NPN SILICON RF TRANSISTOR

### DESCRIPTION:

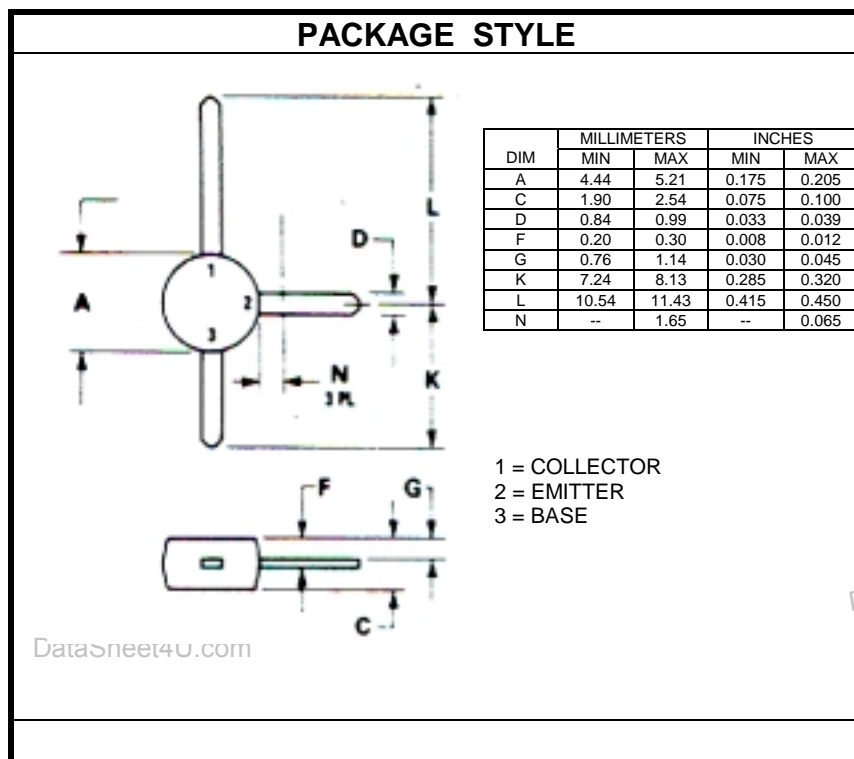
The **ASI MRF962** is designed for Low-to-medium power amplifier applications, requiring high gain, low noise figure, and low intermodulation distortion.

### FEATURES:

- **NF** = 2.0 dB
- **Omnigold™** Metalization System
- Hermetic stripline, ceramic package

### MAXIMUM RATINGS

$I_C$	100 mA
$V_{CB}$	20 V
$P_{DISS}$	.75 W @ $T_C = 100\text{ }^\circ\text{C}$
$T_J$	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
$T_{STG}$	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
$\theta_{JC}$	133 $^\circ\text{C/W}$



### CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 1.0\text{ mA}$			15			V
$BV_{CBO}$	$I_C = 100\text{ }\mu\text{A}$			20			V
$BV_{EBO}$	$I_E = 100\text{ }\mu\text{A}$			3.0			V
$I_{CBO}$	$V_{CB} = 10\text{ V}$					100	nA
$h_{FE}$	$V_{CE} = 10\text{ V}$	$I_C = 50\text{ mA}$		30		200	---
$C_{CB}$	$V_{CB} = 10\text{ V}$	$f = 1.0\text{ MHz}$			1.2	1.5	pF
$f_t$	$V_{CE} = 10\text{ V}$	$I_C = 50\text{ mA}$	$f = 0.5\text{ GHz}$		4.5		GHz
<b>NF</b>	$V_{CE} = 10\text{ V}$	$I_C = 10\text{ mA}$	$f = 0.5\text{ GHz}$		2.0		dB